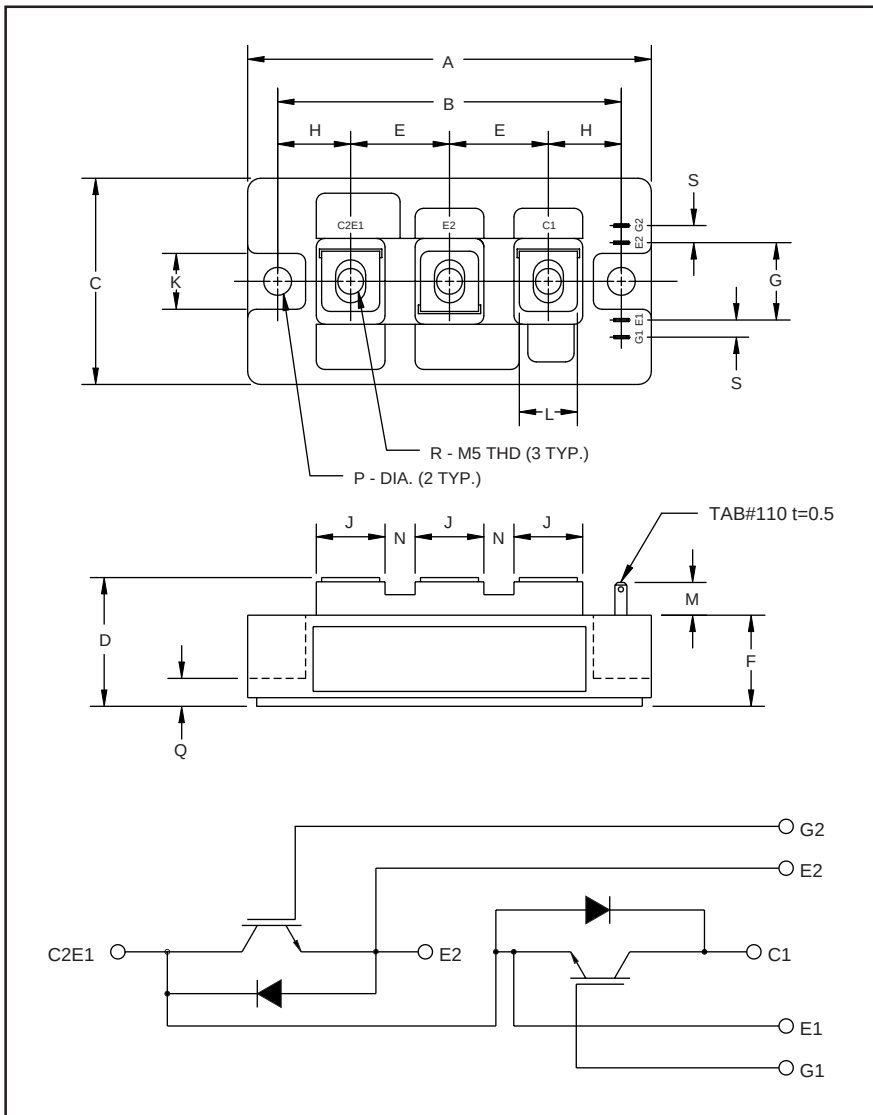


**MITSUBISHI IGBT MODULES**  
**CM200DY-12H**  
HIGH POWER SWITCHING USE  
INSULATED TYPE



**Outline Drawing and Circuit Diagram**

| Dimensions | Inches     | Millimeters |
|------------|------------|-------------|
| A          | 3.70       | 94.0        |
| B          | 3.150±0.01 | 80.0±0.25   |
| C          | 1.89       | 48.0        |
| D          | 1.18 Max.  | 30.0 Max.   |
| E          | 0.90       | 23.0        |
| F          | 0.83       | 21.2        |
| G          | 0.71       | 18.0        |
| H          | 0.67       | 17.0        |
| J          | 0.63       | 16.0        |

| Dimensions | Inches     | Millimeters |
|------------|------------|-------------|
| K          | 0.51       | 13.0        |
| L          | 0.47       | 12.0        |
| M          | 0.30       | 7.5         |
| N          | 0.28       | 7.0         |
| P          | 0.256 Dia. | Dia. 6.5    |
| Q          | 0.31       | 8.0         |
| R          | M5 Metric  | M5          |
| S          | 0.16       | 4.0         |



**Description:**

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of two IGBTs in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

**Features:**

- ☐ Low Drive Power
- ☐ Low  $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ High Frequency Operation
- ☐ Isolated Baseplate for Easy Heat Sinking

**Applications:**

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies

**Ordering Information:**

Example: Select the complete part module number you desire from the table below -i.e. CM200DY-12H is a 600V ( $V_{CES}$ ), 200 Ampere Dual IGBT Module.

| Type | Current Rating<br>Amperes | $V_{CES}$<br>Volts (x 50) |
|------|---------------------------|---------------------------|
| CM   | 200                       | 12                        |

**CM200DY-12H****HIGH POWER SWITCHING USE  
INSULATED TYPE****Absolute Maximum Ratings,  $T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified**

|                                                                                               | Symbol           | Ratings     | Units              |
|-----------------------------------------------------------------------------------------------|------------------|-------------|--------------------|
| Junction Temperature                                                                          | $T_j$            | -40 to 150  | $^{\circ}\text{C}$ |
| Storage Temperature                                                                           | $T_{\text{stg}}$ | -40 to 125  | $^{\circ}\text{C}$ |
| Collector-Emitter Voltage (G-E SHORT)                                                         | $V_{\text{CES}}$ | 600         | Volts              |
| Gate-Emitter Voltage (C-E SHORT)                                                              | $V_{\text{GES}}$ | $\pm 20$    | Volts              |
| Collector Current ( $T_C = 25^{\circ}\text{C}$ )                                              | $I_C$            | 200         | Amperes            |
| Peak Collector Current                                                                        | $I_{\text{CM}}$  | 400*        | Amperes            |
| Emitter Current** ( $T_C = 25^{\circ}\text{C}$ )                                              | $I_E$            | 200         | Amperes            |
| Peak Emitter Current**                                                                        | $I_{\text{EM}}$  | 400*        | Amperes            |
| Maximum Collector Dissipation ( $T_C = 25^{\circ}\text{C}$ , $T_j \leq 150^{\circ}\text{C}$ ) | $P_C$            | 780         | Watts              |
| Mounting Torque, M5 Main Terminal                                                             | —                | 1.47 ~ 1.96 | N · m              |
| Mounting Torque, M6 Mounting                                                                  | —                | 1.96 ~ 2.94 | N · m              |
| Weight                                                                                        | —                | 270         | Grams              |
| Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)                                     | $V_{\text{iso}}$ | 2500        | Vrms               |

\*Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(\text{max})}$  rating.

\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

**Static Electrical Characteristics,  $T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified**

| Characteristics                      | Symbol               | Test Conditions                                                                    | Min. | Typ. | Max.  | Units         |
|--------------------------------------|----------------------|------------------------------------------------------------------------------------|------|------|-------|---------------|
| Collector-Cutoff Current             | $I_{\text{CES}}$     | $V_{\text{CE}} = V_{\text{CES}}$ , $V_{\text{GE}} = 0\text{V}$                     | —    | —    | 1.0   | mA            |
| Gate Leakage Current                 | $I_{\text{GES}}$     | $V_{\text{GE}} = V_{\text{GES}}$ , $V_{\text{CE}} = 0\text{V}$                     | —    | —    | 0.5   | $\mu\text{A}$ |
| Gate-Emitter Threshold Voltage       | $V_{\text{GE(th)}}$  | $I_C = 20\text{mA}$ , $V_{\text{CE}} = 10\text{V}$                                 | 4.5  | 6.0  | 7.5   | Volts         |
| Collector-Emitter Saturation Voltage | $V_{\text{CE(sat)}}$ | $I_C = 200\text{A}$ , $V_{\text{GE}} = 15\text{V}$                                 | —    | 2.1  | 2.8** | Volts         |
|                                      |                      | $I_C = 200\text{A}$ , $V_{\text{GE}} = 15\text{V}$ , $T_j = 150^{\circ}\text{C}$   | —    | 2.15 | —     | Volts         |
| Total Gate Charge                    | $Q_G$                | $V_{\text{CC}} = 300\text{V}$ , $I_C = 200\text{A}$ , $V_{\text{GE}} = 15\text{V}$ | —    | 600  | —     | nC            |
| Emitter-Collector Voltage            | $V_{\text{EC}}$      | $I_E = 200\text{A}$ , $V_{\text{GE}} = 0\text{V}$                                  | —    | —    | 2.8   | Volts         |

\*\* Pulse width and repetition rate should be such that device junction temperature rise is negligible.

**Dynamic Electrical Characteristics,  $T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified**

| Characteristics               | Symbol              | Test Conditions                                                                                                             | Min. | Typ. | Max. | Units         |
|-------------------------------|---------------------|-----------------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| Input Capacitance             | $C_{\text{ies}}$    |                                                                                                                             | —    | —    | 20   | nF            |
| Output Capacitance            | $C_{\text{oes}}$    | $V_{\text{GE}} = 0\text{V}$ , $V_{\text{CE}} = 10\text{V}$                                                                  | —    | —    | 7    | nF            |
| Reverse Transfer Capacitance  | $C_{\text{res}}$    |                                                                                                                             | —    | —    | 4    | nF            |
| Resistive                     | Turn-on Delay Time  | $V_{\text{CC}} = 300\text{V}$ , $I_C = 200\text{A}$ ,<br>$V_{\text{GE1}} = V_{\text{GE2}} = 15\text{V}$ , $R_G = 3.1\Omega$ | —    | —    | 200  | ns            |
| Load                          | Rise Time           |                                                                                                                             | —    | —    | 550  | ns            |
| Switching                     | Turn-off Delay Time |                                                                                                                             | —    | —    | 300  | ns            |
| Times                         | Fall Time           |                                                                                                                             | —    | —    | 300  | ns            |
| Diode Reverse Recovery Time   | $t_{\text{rr}}$     | $I_E = 200\text{A}$ , $di_E/dt = -400\text{A}/\mu\text{s}$                                                                  | —    | —    | 110  | ns            |
| Diode Reverse Recovery Charge | $Q_{\text{rr}}$     | $I_E = 200\text{A}$ , $di_E/dt = -400\text{A}/\mu\text{s}$                                                                  | —    | 0.54 | —    | $\mu\text{C}$ |

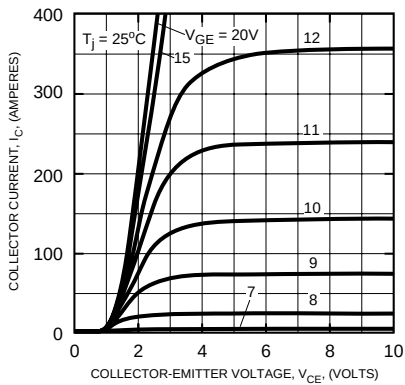
**Thermal and Mechanical Characteristics,  $T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified**

| Characteristics                      | Symbol               | Test Conditions                    | Min. | Typ. | Max.  | Units                       |
|--------------------------------------|----------------------|------------------------------------|------|------|-------|-----------------------------|
| Thermal Resistance, Junction to Case | $R_{\text{th(j-c)}}$ | Per IGBT                           | —    | —    | 0.16  | $^{\circ}\text{C}/\text{W}$ |
| Thermal Resistance, Junction to Case | $R_{\text{th(j-c)}}$ | Per FWDi                           | —    | —    | 0.35  | $^{\circ}\text{C}/\text{W}$ |
| Contact Thermal Resistance           | $R_{\text{th(c-f)}}$ | Per Module, Thermal Grease Applied | —    | —    | 0.065 | $^{\circ}\text{C}/\text{W}$ |

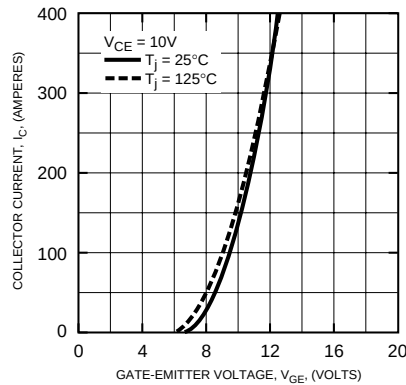
# CM200DY-12H

HIGH POWER SWITCHING USE  
INSULATED TYPE

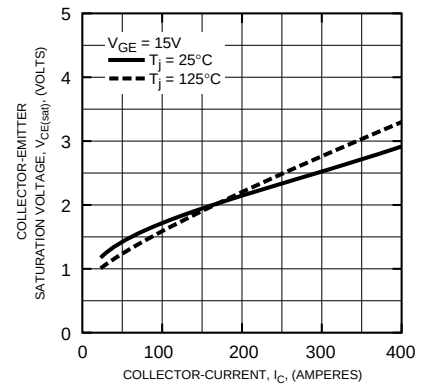
OUTPUT CHARACTERISTICS  
(TYPICAL)



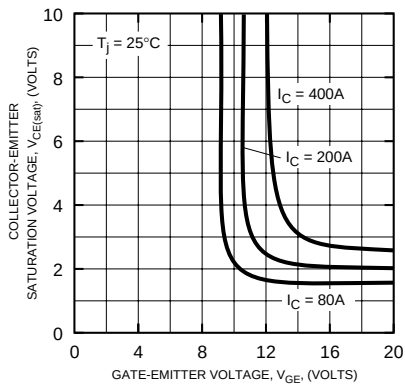
TRANSFER CHARACTERISTICS  
(TYPICAL)



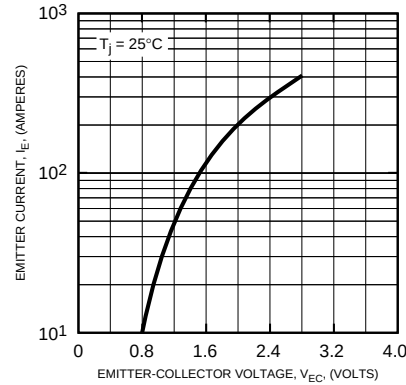
COLLECTOR-EMITTER  
SATURATION VOLTAGE CHARACTERISTICS  
(TYPICAL)



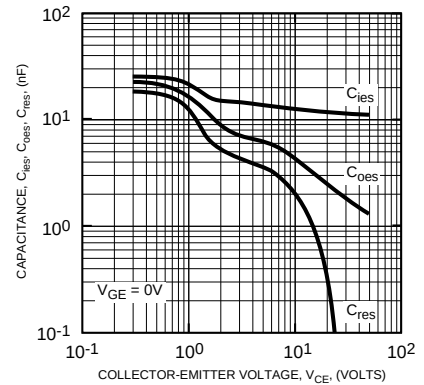
COLLECTOR-EMITTER  
SATURATION VOLTAGE CHARACTERISTICS  
(TYPICAL)



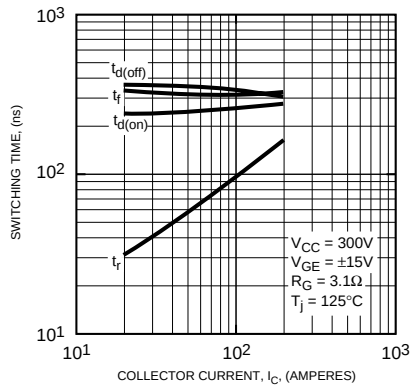
FREE-WHEEL DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)



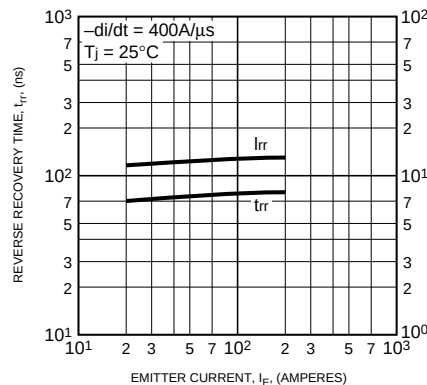
CAPACITANCE VS.  $V_{CE}$   
(TYPICAL)



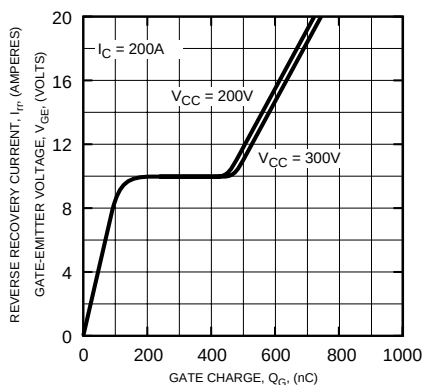
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS  
(TYPICAL)



GATE CHARGE,  $V_{GE}$



# CM200DY-12H

HIGH POWER SWITCHING USE  
INSULATED TYPE

